| L Number | | Search Text | DB | Time stamp |
|----------|--------|--|-----------|-------------------|
| 9 | 655258 | H01L\$4 | EPO; JPO; | 2003/05/05 02:1 |
| | | | DERWENT | |
| 10 | 366362 | H01L\$4 and semiconductor | EPO; JPO; | 2003/05/05 02:1 |
| | | | DERWENT | |
| 11 | 523 | (H01L\$4 and semiconductor) and (self adj | EPO; JPO; | 2003/05/05 02:1 |
| | | aligned adj contact) | DERWENT | |
| 12 | 2 | ((H01L\$4 and semiconductor) and (self adj | EPO; JPO; | 2003/05/05 02:1 |
| | | aligned adj contact)) and (stopping adj | DERWENT | 1 |
| 111 | | layer) | | 1 |
| 15 | 1748 | self adj (aligned or aligning or aligns or | USPAT | 2003/05/05 02:2 |
| 1 | | align) adj (contact or contacts) | | |
| 16 | 67 | (self adj (aligned or aligning or aligns | USPAT | 2003/05/05 02:4 |
| | | or align) adj (contact or contacts)) and | | |
| | | ((dry adj etch\$3) with (interdielectric or | | |
| | | dielectric)) | | |
| 17 | 0 | planarizing with (gate adj upper adj | USPAT | 2003/05/05 02:4 |
| | | dielectric) | | |
| 18 | 0 | planarize with (gate adj upper adj | USPAT | 2003/05/05 02:4 |
| | | dielectric) | 1 | |
| 19 | 0 | planar\$5 with (gate adj upper adj | USPAT | 2003/05/05 02:4 |
| | | dielectric) | | |
| 20 | 1 | gate adj upper adj dielectric | USPAT | 2003/05/05 02:4 |
| 21 | | gate adj dielectric | USPAT | 2003/05/05 02:4 |
| 22 | 33 | planarizing with (gate adj dielectric) | USPAT | 2003/05/05 02:4 |
| 23 | 8 | planarize with (gate adj dielectric) | USPAT | 2003/05/05 02:4 |
| 24 | 157 | 1 - | USPAT | 2003/05/05 02:4 |
| 25 | 120 | (planar\$5 with (gate adj dielectric)) not | USPAT | 2003/05/05 02:4 |
| | | ((planarize with (gate adj dielectric)) or | | |
| 1 | | (planarizing with (gate adj dielectric))) | | |
| 29 | 8 | (("6313018") or ("6287957") or ("6165901") | USPAT | 2003/05/05 03:4 |
| 23 | O | or ("6204161") or ("6507064") or | OBIAI | 2003,03,03 |
| | | ("6468859") or ("6380042") or | | |
| | | ("6081016")).PN. | | |
| | 5027 | (gate adj electrode) and ((dry adj | USPAT | 2003/05/03 21:1 |
| | 3927 | etching) or CMP or (chemical adj | OSFAI | , 2003/03/03 21:1 |
| | | mechanical adj polishing)) | | , |
| | 19 | | USPAT | 2002/06/30 17:5 |
| | 19 | and ((dry adj etching) or CMP or (chemical | USIAI | 2002/00/30 17:3 |
| 100 | | adj mechanical adj polishing)) | 1 | İ |
| | 31 | 1 - | USPAT | 2002/06/30 18:0 |
| | 31 | etching) or CMP or (chemical adj | OSTAI | 2002/00/30 10:0 |
| | | mechanical adj polishing)) | | |
| | 1945 | 438/586.ccls. or 438/587.ccls. or | USPAT | 2003/04/16 15:0 |
| | 1943 | 438/595.ccls. or 438/597.ccls. or | ODIAI | 2003/04/10 13:0 |
| | | The state of the s | | |
| | 214 | 438/598.ccls. 438/584.ccls. | USPAT | 2003/04/16 15:0 |
| | 1650 | 438/666.ccls. or 438/669.ccls. or | USPAT | 2003/04/10 13:0 |
| | 1020 | 438/674.ccls. or 438/684.ccls. or | JULAI | 2003/03/03 02.1 |
| | | 438/685.ccls. | | 1 |
| | 1791 | (438/586.ccls. or 438/587.ccls. or | USPAT | 2003/05/05 03:1 |
| | 1/21 | 438/595.ccls. or 438/597.ccls. or | 30171 | 2003/03/03 03.1 |
| | | 438/598.ccls. or 438/597.ccls. or 438/598.ccls. or | | |
| | | (438/598.ccis.) not (438/584.ccis. or (438/669.ccls. or | | |
| | | 438/674.ccls. or 438/684.ccls. or | | |
| | | | | |
| 1 | 155 | 438/685.ccls.)) | HODAM | 2003/04/16 15:5 |
| | 1/5 | 438/584.ccls. not ((438/586.ccls. or | USPAT | 2003/04/10 13.3 |
| | | 438/587.ccls. or 438/595.ccls. or | i | 1 |
| 1 | | 438/597.ccls. or 438/598.ccls.) or | | i |
| | | (438/666.ccls. or 438/669.ccls. or | | |
| i | | 438/674.ccls. or 438/684.ccls. or | | |
| | | 438/685.ccls.)) | HCDAG | 2002/04/16 16-5 |
| - | 1514 | (438/666.ccls. or 438/669.ccls. or | USPAT | 2003/04/16 16:5 |
| | | 438/674.ccls. or 438/684.ccls. or | | |
| | | 438/685.ccls.) not ((438/586.ccls. or | | |
| | | 438/587.ccls. or 438/595.ccls. or | | |
| | | 438/597.ccls. or 438/598.ccls.) or | | 1 |
| | | 438/584.ccls.) | | 0000 105 100 01 5 |
| - | 290389 | gate | USPAT | 2003/05/03 21:1 |
| - | 21471 | gate and ((stopping or (stopping layer)) | USPAT | 2003/05/03 21:4 |
| | | with (nitride or (silicon adj nitride))) | | |

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| | 13415 | (gate and ((stopping or (stopping layer)) | USPAT | 2003/05/03 21:21 |
|---|-------|--|-------|------------------|
| | | with (nitride or (silicon adj nitride)))) and (dielectric or interdielectric) | | |
| _ | 1564 | ((gate and ((stopping or (stopping layer)) with (nitride or (silicon adj nitride)))) | USPAT | 2003/05/03 21:22 |
| | | and (dielectric or interdielectric)) and | | 1 |
| | | (planariz\$3 with ((dry adj etching) or CMP)) | | |
| _ | 630 | <pre>(((gate and ((stopping or (stopping layer)) with (nitride or (silicon adj nitride)))) and (dielectric or interdielectric)) and (planariz\$3 with ((dry adj etching) or CMP))) and (conductive with ((doped adj polysilicon) or titanium or (titanium adj nitride) or tungsten))</pre> | USPAT | 2003/05/03 21:39 |
| _ | 89 | | USPAT | 2003/05/03 21:23 |
| | 541 | | USPAT | 2003/05/03 21:46 |
| - | 21 | | USPAT | 2003/05/03 21:48 |
| - | 1665 | self adj (aligned or aligning or aligns) adj (contact or contacts) | USPAT | 2003/05/03 21:54 |